

NTHD3100C

Power MOSFET

20 V, +3.9 A / -4.4 A,
Complementary ChipFET™

Features

- Complementary N-Channel and P-Channel MOSFET
- Small Size, 40% Smaller than TSOP-6 Package
- Leadless SMD Package Provides Great Thermal Characteristics
- Trench P-Channel for Low On Resistance
- Low Gate Charge N-Channel for Test Switching
- Pb-Free Packages are Available

Applications

- DC-DC Conversion Circuits
- Load Switch Applications Requiring Level Shift
- Drive Small Brushless DC Motors
- Ideal for Power Management Applications in Portable, Battery Powered Products

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	20	V
Gate-to-Source Voltage	N-Ch	±12	V
	P-Ch	±8.0	V
N-Channel Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	A
		T _A = 85°C	
	t ≤ 10 s	T _A = 25°C	
P-Channel Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	A
		T _A = 85°C	
	t ≤ 10 s	T _A = 25°C	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	W
Pulsed Drain Current (Note 1)	N-Ch	t = 10 μs	A
	P-Ch	t = 10 μs	
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to 150	°C
Source Current (Body Diode)	I _S	2.5	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 seconds)	T _L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

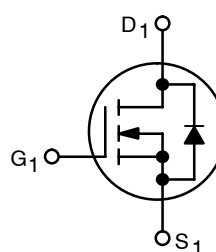
1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).



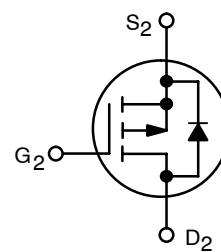
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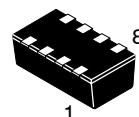
V _{(BR)DSS}	R _{DS(on)} Typ	I _D MAX
N-Channel 20 V	58 mΩ @ 4.5 V	3.9 A
	77 mΩ @ 2.5 V	
P-Channel -20 V	64 mΩ @ -4.5 V	-4.4 A
	85 mΩ @ -2.5 V	



N-Channel MOSFET

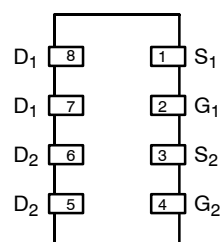


P-Channel MOSFET

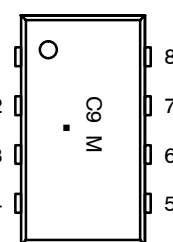


ChipFET
CASE 1206A
STYLE 2

PIN CONNECTIONS



MARKING DIAGRAM



C9 = Specific Device Code
M = Month Code
▪ = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

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THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	113	$^{\circ}\text{C/W}$
Junction-to-Ambient – $t \leq 10$ s (Note 2)	$R_{\theta JA}$	60	$^{\circ}\text{C/W}$

2. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	N/P	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS (Note 3)							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	N	$V_{GS} = 0$ V	$I_D = 250$ μA	20		V
		P		$I_D = -250$ μA	-20		
Zero Gate Voltage Drain Current	I_{DSS}	N	$V_{GS} = 0$ V, $V_{DS} = 16$ V	$T_J = 25^{\circ}\text{C}$		1.0	μA
		P	$V_{GS} = 0$ V, $V_{DS} = -16$ V			-1.0	
		N	$V_{GS} = 0$ V, $V_{DS} = 16$ V	$T_J = 125^{\circ}\text{C}$		5.0	
		P	$V_{GS} = 0$ V, $V_{DS} = -16$ V			-5.0	
Gate-to-Source Leakage Current	I_{GSS}	N	$V_{DS} = 0$ V, $V_{GS} = \pm 12$ V			± 100	nA
		P	$V_{DS} = 0$ V, $V_{GS} = \pm 8.0$ V			± 100	

ON CHARACTERISTICS

 (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	N	$V_{GS} = V_{DS}$	$I_D = 250\text{ }\mu\text{A}$	0.6		1.2	V
		P		$I_D = -250\text{ }\mu\text{A}$	-.45		-1.5	
Drain-to-Source On Resistance	$R_{DS(on)}$	N	$V_{GS} = 4.5\text{ V}$, $I_D = 2.9\text{ A}$			58	80	m Ω
		P	$V_{GS} = -4.5\text{ V}$, $I_D = -3.2\text{ A}$			64	80	
		N	$V_{GS} = 2.5\text{ V}$, $I_D = 2.3\text{ A}$			77	115	
		P	$V_{GS} = -2.5\text{ V}$, $I_D = -2.2\text{ A}$			85	110	
Forward Transconductance	g_{FS}	N	$V_{DS} = 10\text{ V}$, $I_D = 2.9\text{ A}$			6.0		S
		P	$V_{DS} = -10\text{ V}$, $I_D = -3.2\text{ A}$			8.0		

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	N	$f = 1$ MHz, $V_{GS} = 0$ V	$V_{DS} = 10$ V		165	pF
		P		$V_{DS} = -10$ V		680	
Output Capacitance	C_{OSS}	N		$V_{DS} = 10$ V		80	
		P		$V_{DS} = -10$ V		100	
Reverse Transfer Capacitance	C_{RSS}	N		$V_{DS} = 10$ V		25	
		P		$V_{DS} = -10$ V		70	
Total Gate Charge	$Q_{G(TOT)}$	N		$V_{GS} = 4.5$ V, $V_{DS} = 10$ V, $I_D = 2.9$ A		2.3	nC
		P		$V_{GS} = -4.5$ V, $V_{DS} = -10$ V, $I_D = -3.2$ A		7.4	
Threshold Gate Charge	$Q_{G(TH)}$	N		$V_{GS} = 4.5$ V, $V_{DS} = 10$ V, $I_D = 2.9$ A		0.2	
		P		$V_{GS} = -4.5$ V, $V_{DS} = -10$ V, $I_D = -3.2$ A		0.6	
Gate-to-Source Gate Charge	Q_{GS}	N		$V_{GS} = 4.5$ V, $V_{DS} = 10$ V, $I_D = 2.9$ A		0.4	
		P		$V_{GS} = -4.5$ V, $V_{DS} = -10$ V, $I_D = -3.2$ A		1.4	
Gate-to-Drain "Miller" Charge	Q_{GD}	N		$V_{GS} = 4.5$ V, $V_{DS} = 10$ V, $I_D = 2.9$ A		0.7	
		P		$V_{GS} = -4.5$ V, $V_{DS} = -10$ V, $I_D = -3.2$ A		2.5	

3. Pulse Test: pulse width ≤ 250 μs , duty cycle $\leq 2\%$.

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ELECTRICAL CHARACTERISTICS (continued) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	N/P	Test Conditions	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 4)							
Turn-On Delay Time	$t_{d(ON)}$	N	$V_{GS} = 4.5\text{ V}, V_{DD} = 10\text{ V},$ $I_D = 2.9\text{ A}, R_G = 2.5\ \Omega$		6.3		ns
Rise Time	t_r				10.7		
Turn-Off Delay Time	$t_{d(OFF)}$				9.6		
Fall Time	t_f				1.5		
Turn-On Delay Time	$t_{d(ON)}$	P	$V_{GS} = -4.5\text{ V}, V_{DD} = -10\text{ V},$ $I_D = -3.2\text{ A}, R_G = 2.5\ \Omega$		5.8		
Rise Time	t_r				11.7		
Turn-Off Delay Time	$t_{d(OFF)}$				16		
Fall Time	t_f				12.4		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	N	$V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	$I_S = 2.5\text{ A}$		0.8	1.15	V
		P		$I_S = -2.5\text{ A}$		-0.8	-1.2	
Reverse Recovery Time	t_{RR}	N	$V_{GS} = 0\text{ V},$ $dI_S / dt = 100\text{ A}/\mu\text{s}$	$I_S = 1.5\text{ A}$		12.5		ns
		P		$I_S = -1.5\text{ A}$		13.5		
Charge Time	t_a	N		$I_S = 1.5\text{ A}$		9.0		
		P		$I_S = -1.5\text{ A}$		9.5		
Discharge Time	t_b	N		$I_S = 1.5\text{ A}$		3.5		
		P		$I_S = -1.5\text{ A}$		4.0		
Reverse Recovery Charge	Q_{RR}	N		$I_S = 1.5\text{ A}$		6.0		nC
		P		$I_S = -1.5\text{ A}$		6.5		

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL N-CHANNEL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

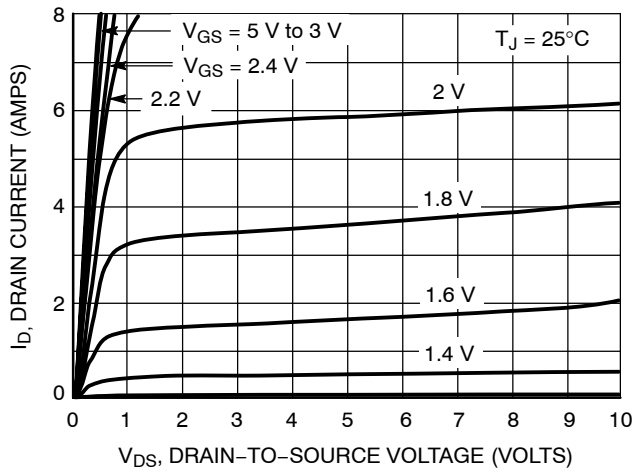


Figure 1. On-Region Characteristics

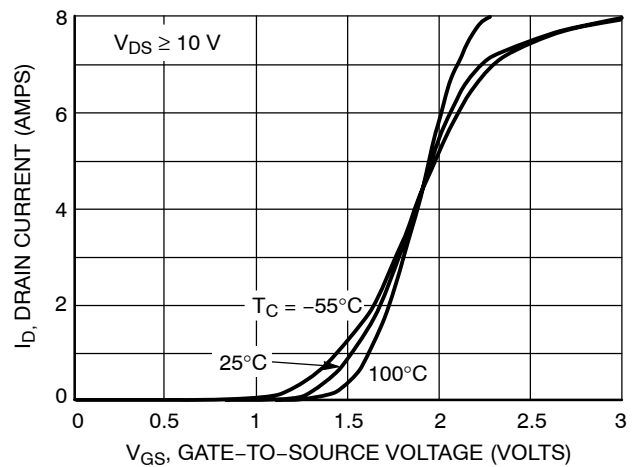


Figure 2. Transfer Characteristics

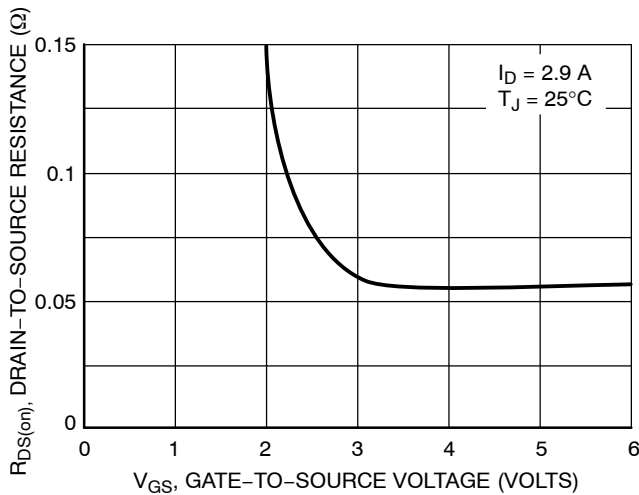


Figure 3. On-Resistance vs. Gate-to-Source Voltage

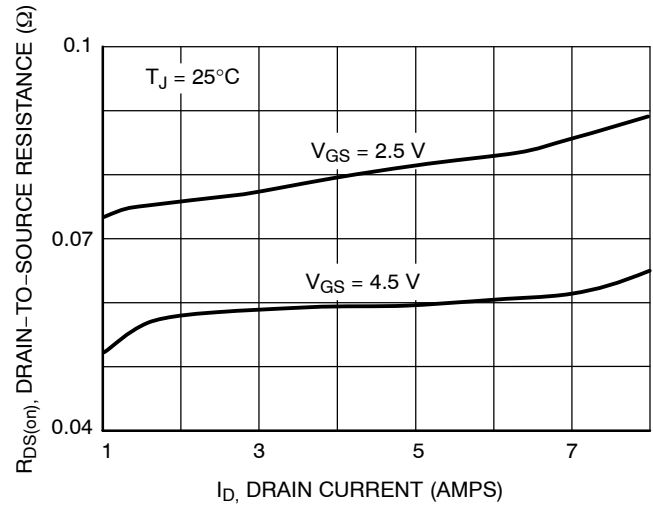


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

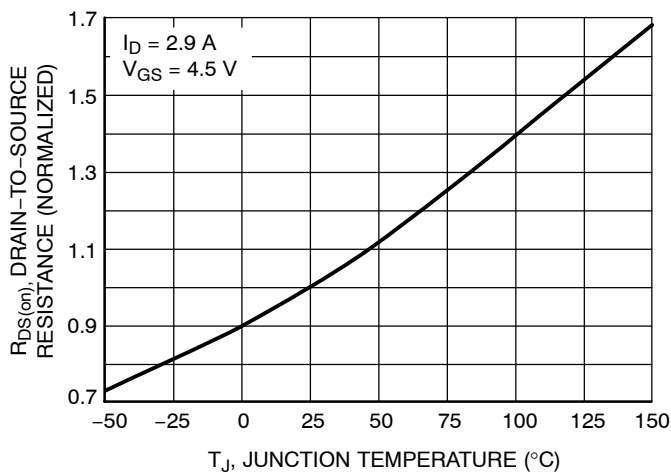


Figure 5. On-Resistance Variation with Temperature

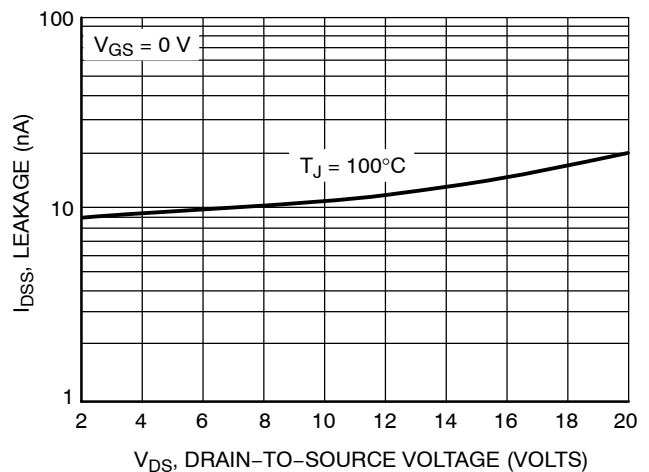
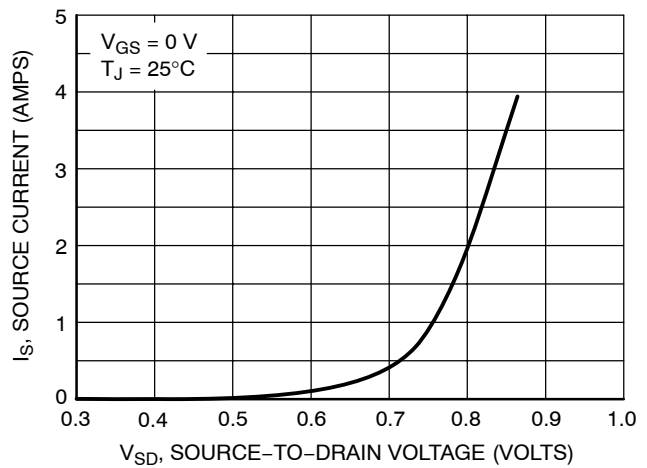
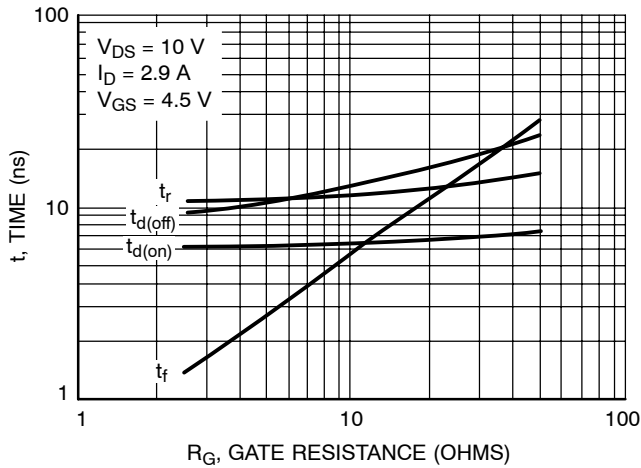
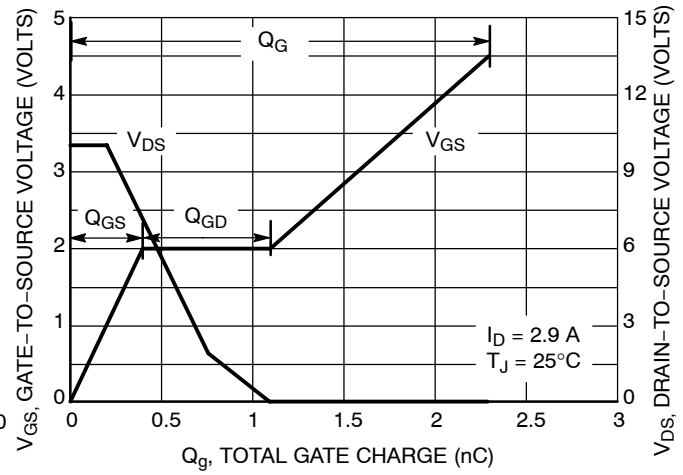
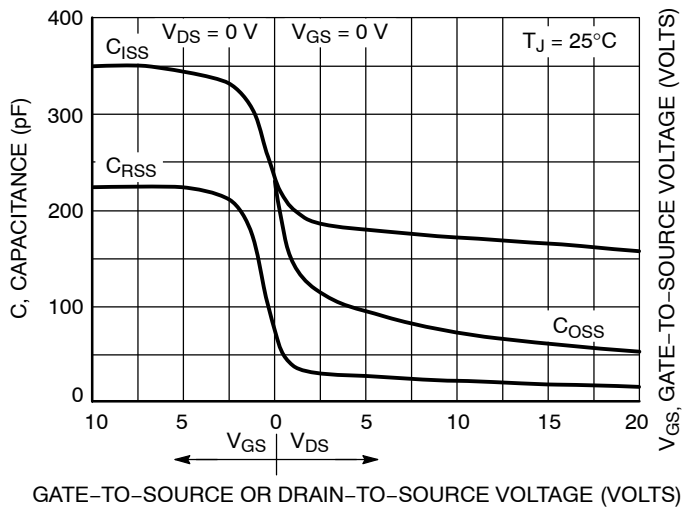


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL N-CHANNEL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)



TYPICAL P-CHANNEL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

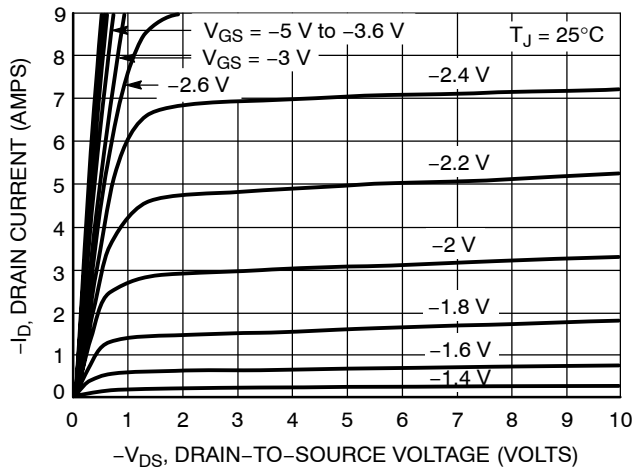


Figure 11. On-Region Characteristics

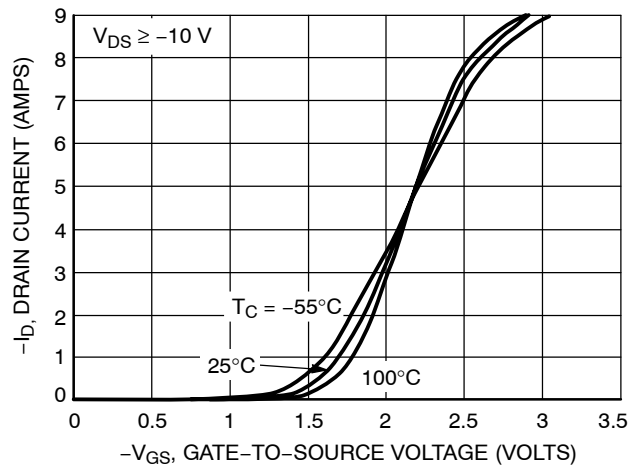


Figure 12. Transfer Characteristics

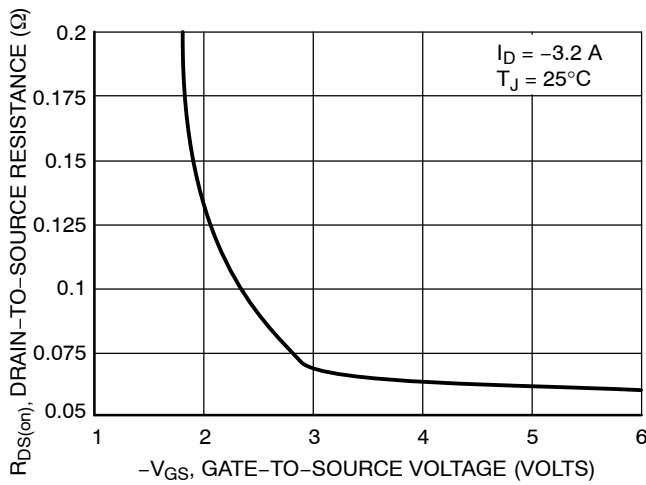


Figure 13. On-Resistance vs. Gate-to-Source Voltage

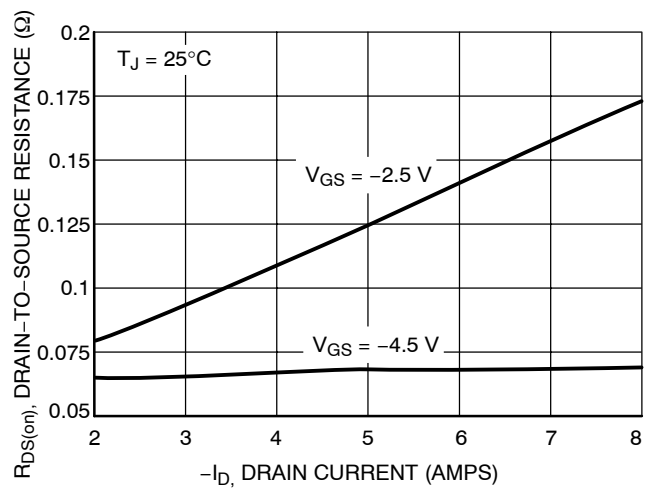


Figure 14. On-Resistance vs. Drain Current and Gate Voltage

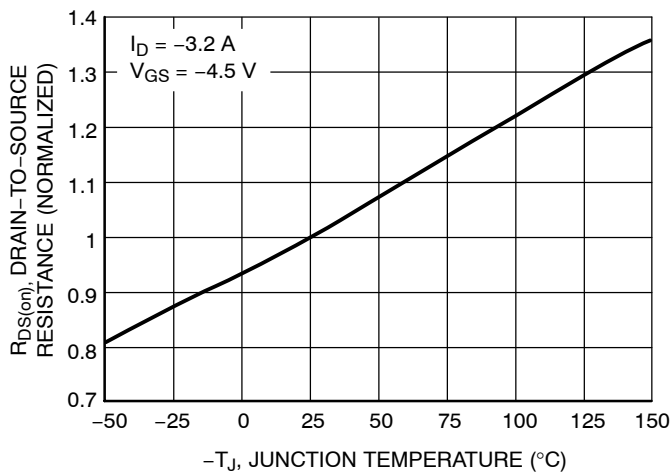


Figure 15. On-Resistance Variation with Temperature

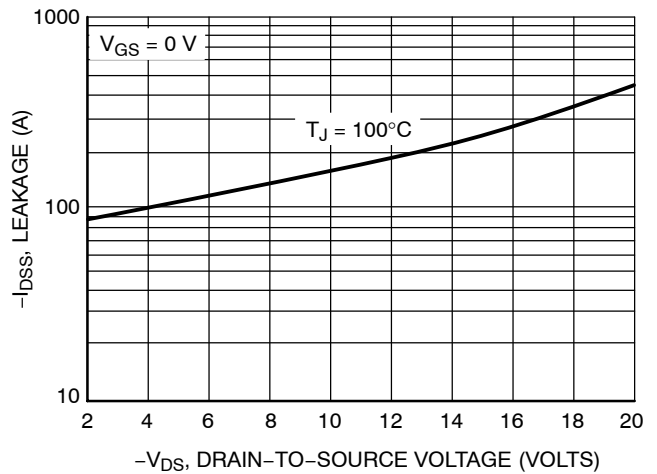


Figure 16. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL P-CHANNEL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

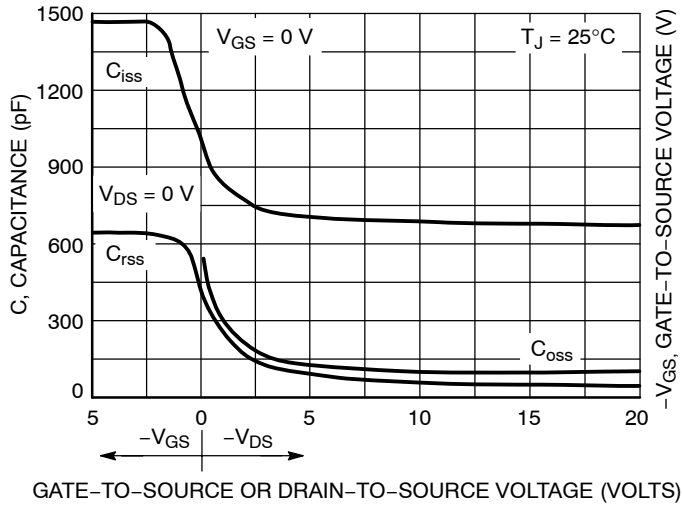


Figure 17. Capacitance Variation

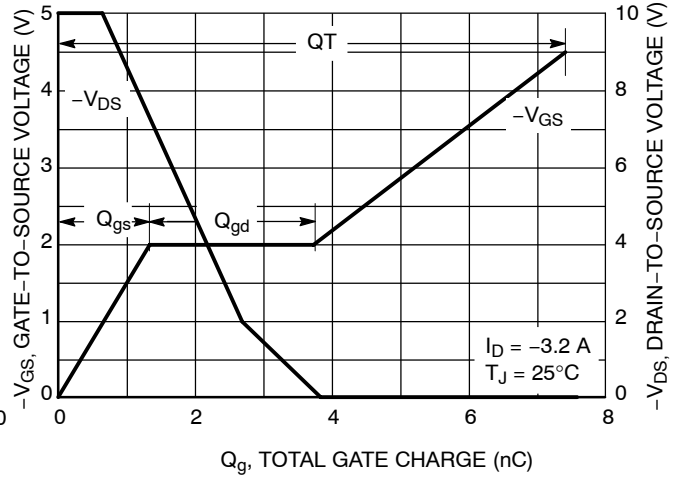


Figure 18. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

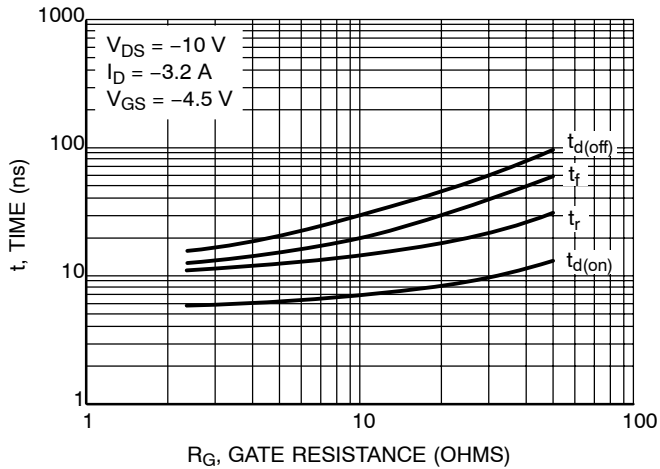


Figure 19. Resistive Switching Time Variation vs. Gate Resistance

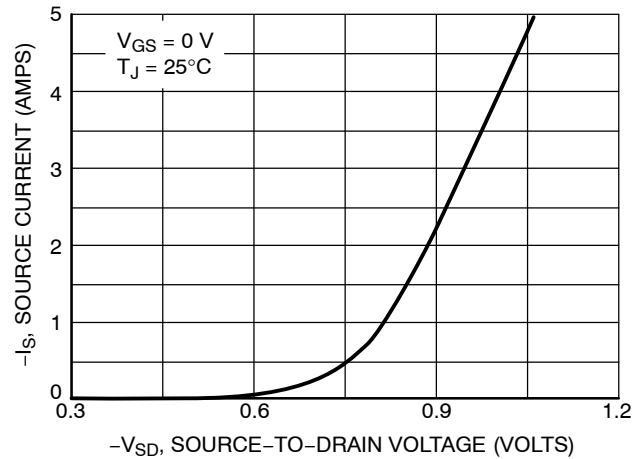


Figure 20. Diode Forward Voltage vs. Current

DEVICE ORDERING INFORMATION

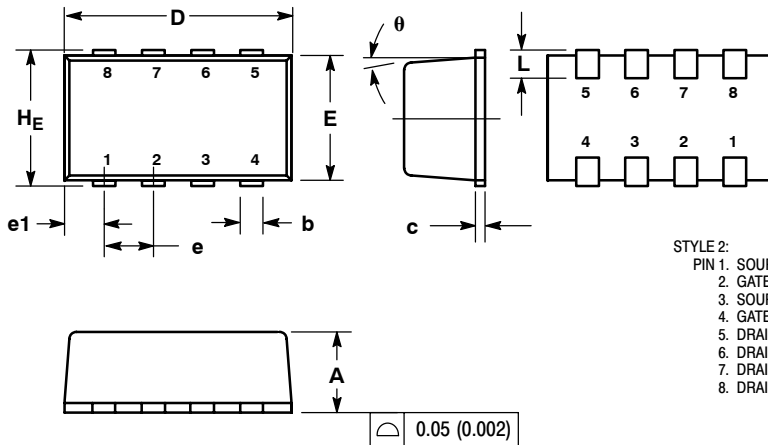
Device	Package	Shipping [†]
NTHD3100CT1	ChipFET	3000 / Tape & Reel
NTHD3100CT1G	ChipFET (Pb-Free)	3000 / Tape & Reel
NTHD3100CT3	ChipFET	10000 / Tape & Reel
NTHD3100CT3G	ChipFET (Pb-Free)	10000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTHD3100C

PACKAGE DIMENSIONS

ChipFET™
CASE 1206A-03
ISSUE G

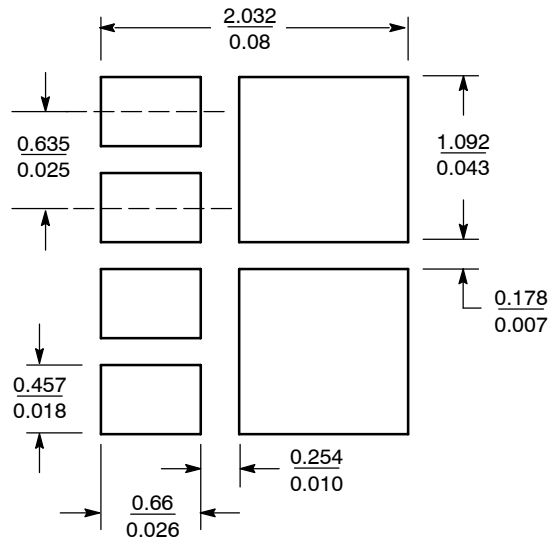


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.05	1.10	0.039	0.041	0.043
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	1.55	1.65	1.70	0.061	0.065	0.067
e	0.65 BSC			0.025 BSC		
e1	0.55 BSC			0.022 BSC		
L	0.28	0.35	0.42	0.011	0.014	0.017
HE	1.80	1.90	2.00	0.071	0.075	0.079
θ	5° NOM			5° NOM		

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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